

isc Silicon NPN Power Transistor

KSD5017

DESCRIPTION

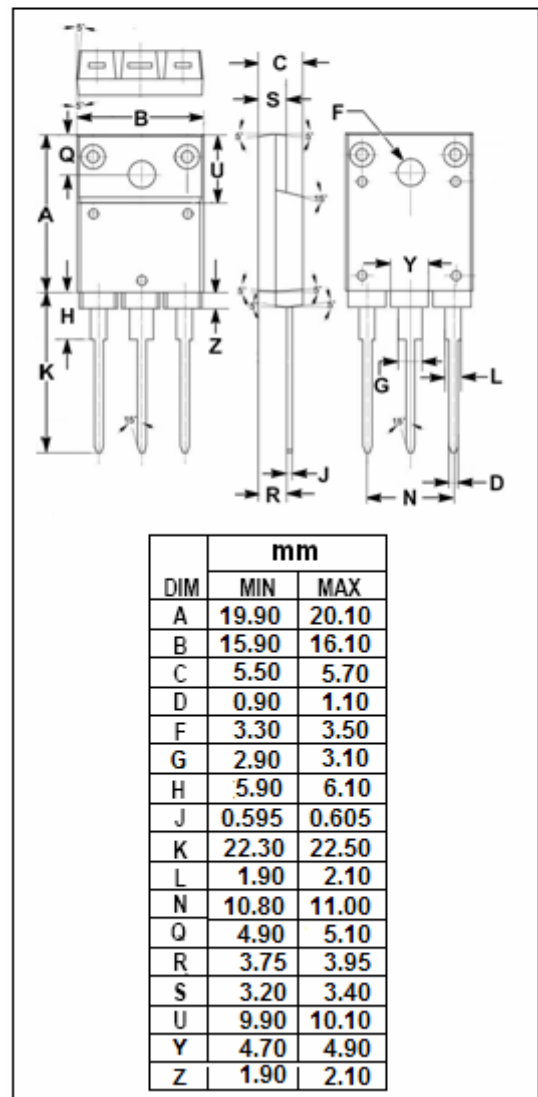
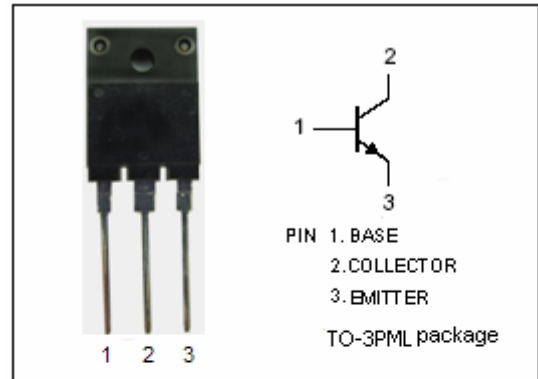
- High Breakdown Voltage-  
:  $V_{CBO} = 1500V$  (Min)
- High Switching Speed
- High Reliability

APPLICATIONS

- Designed for color TV horizontal output applications

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current- Continuous	6	A
$I_{CP}$	Collector Current-Peak	16	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ C$	60	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



**isc Silicon NPN Power Transistor****KSD5017****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=1\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=1\text{A}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=800\text{V}; I_E=0$			10	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			1	mA
$h_{FE}$	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	8			
$f_T$	Current-Gain—Bandwidth Product	$I_C=1\text{A}; V_{CE}=10\text{V}$		3		MHz
$t_f$	Fall Time	$I_C=5\text{A}, I_{B1}=1\text{A}; I_{B2}=-2\text{A}$ $R_L=40\Omega; V_{CC}=200\text{V}$			0.4	$\mu\text{s}$